

Phison Electronics Corporation PS3111-S11 M.2 2280 TLC Specification

Version 2.9



Phison Electronics Corporation

No.1, Qun-Yi Road, Jhunan, Miaoli County, Taiwan 350, R.O.C. Tel: +886-37-586-896 Fax: +886-37-587-868 E-mail: sales@phison.com / suppport@phison.com

Document Number: S-18320



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Revision History

Revision	Draft Date	History	Author
1.0	2016/05/05	First release	Lisa Wu
1.1	2016/05/20	Add full capacity performance	Lisa Wu
1.2	2016/05/26	Update performance, power consumption and chapter 6 supported command	Lisa Wu
1.3	2016/07/19	Update performance, power consumption and Chapter 8 product Warranty policy	Ichen Yang
1.4	2016/09/21	Update performance	Lisa Wu
1.5	2016/11/15	Update performance, power consumption	Lisa Wu
1.6	2016/12/28	Update performance, power consumption	Errison Chi
1.7	2017/01/11	Update performance, power consumption	Errison Chi
1.8	2017/01/12	Update performance, power consumption	Errison Chi
1.9	2017/01/16	Update performance, power consumption, ESD	Errison Chi
2.0	2017/05/08	Update performance, power consumption	Joe Leng
2.1	2017/05/11	Update performance, power consumption	Joe Leng
2.2	2017/06/30	Update performance, power consumption	Joe Leng
2.3	2017/09/25	Update performance, power consumption	Joe Leng
2.4	2017/09/29	Update performance, power consumption	Joe Leng
2.5	2017/10/03	Update performance, power consumption	Wayne Chen
2.6	2018/01/23	Update performance, power consumption	Wayne Chen
2.7	2018/05/02	Update performance, power consumption	Alvin Chiu
2.8	2018/07/25	Update performance, power consumption Modify the Identify Device Data	Jacky Chien
2.9	2018/12/10	Update performance, power consumption	Claire Chang



Product Overview

- Capacity
 - 16 GB up to 960/1024GB
- Form Factor
 - M.2 2280-S3-B-M
- SATA Interface
 - SATA Revision 3.2
 - SATA 1.5Gbps, 3Gbps, and 6Gbps interface
- Flash Interface
 - Flash type: TLC
 - 1pcs to 4pcs of TSOP/BGA flash
- Performance
 - Read: up to 550 MB/s
 - Write: up to 500 MB/s
- Power Consumption^{Note1}
 - Active mode: < 1,925 mW
 - Idle mode: < 325 mW
 - DEVSLP mode: < 5 mW

- MTBF
 - More than 2,000,000 hours
- Advanced Flash Management
 - Static and Dynamic Wear Leveling
 - Bad Block Management
 - TRIM
 - SMART
 - Over-Provision
 - Firmware Update
 - SmartZIPTM
- Low Power Management
 - DEVSLP Mode (Optional)
 - DIPM/HIPM Mode
- Temperature Range
 - Operation: 0°C ~ 70°C
 - Storage: -40°C ~ 85°C
- RoHS compliant

Notes:

1. Please see "4.2 Power Consumption" for details.



Performance and Power Consumption

		Performance				Power Consumption		
Compositor	Flack Churchina	CrystalDiskMark		AT	ATTO		NA/wit o	DEVCI D
Capacity	Flash Structure	Read	Write	Read	Write	Read	Write (mW)	DEVSLP
		(MB/s)	(MB/s)	(MB/s)	(MB/s)	(mW)		(mW)
120/128GB	32GBx4, TSOP, TSB 15nm	550	450	560	540	1,245	1,375	4.9
120/128GB	64GBx2, TSOP, TSB 15nm	550	460	560	540	1,240	1,370	4.9
240/256GB	64GBx4, TSOP, TSB 15nm	550	450	560	540	1,425	1,850	4.9
480/512GB	128GBx4, TSOP, TSB 15nm	530	410	560	540	1,435	1,600	4.9
240/256GB	128GBx2, BGA, TSB 15nm	550	450	560	540	1,510	1,950	4.9
120GB	64GBx2, BGA, Hynix 16nm	550	380	560	540	1,385	1,600	4.9
240GB	64GBx4, BGA, Hynix 16nm	550	480	560	540	1,685	1,925	4.9
30/32GB	32GBx1, TSOP, TSB BiCS2	290	90	560	540	920	810	4.9
60/64GB	32GBx2, TSOP, TSB BiCS2	550	175	560	540	1,205	1,040	4.9
120/128GB	64GBx2, TSOP, TSB BiCS2	550	350	560	540	1,355	1,400	4.9
240/256GB	64GBx4, TSOP, TSB BiCS2	550	490	560	540	1,400	1,700	4.9
480/512GB	128GBx4, TSOP, TSB BiCS2	550	490	560	540	1,530	1,800	4.9
240/256GB	256GBx1, BGA, TSB BiCS2	550	375	560	540	1,380	1,680	4.9
480/512GB	256GBx2, BGA, TSB BiCS2	550	455	560	540	1,500	1,770	4.9
960/1024GB	256GBx4, BGA, TSB BiCS2	550	490	560	540	1,650	1,880	4.9
16GB	16GBx1, TSOP, TSB BiCS3	290	100	560	540	940	840	4.9
30/32GB	32GBx1, TSOP, TSB BiCS3	300	125	560	540	950	850	4.9
60/64GB	32GBx2, TSOP, TSB BiCS3	550	255	560	540	1,215	1,020	4.9
120/128GB	64GBx2, TSOP, TSB BiCS3	550	450	560	540	1,300	1,350	4.9
240/256GB	64GBx4, TSOP, TSB BiCS3	550	490	560	540	1,350	1,400	4.9
480/512GB	128GBx4, TSOP, TSB BiCS3	550	490	560	540	1,360	1,450	4.9
60/64GB	64GBx1, BGA TSB BiCS3	550	255	560	540	1,200	1,290	4.9
120/128GB	64GBx2, BGA TSB BiCS3	550	450	560	540	1,270	1,360	4.9
240/256GB	64GBx4, BGA TSB BiCS3	550	490	560	540	1,395	1,480	4.9
240/256GB	128GBx2, BGA TSB BiCS3	550	490	560	540	1,360	1,440	4.9
480/512GB	256GBx2, BGA TSB BiCS3	550	490	560	540	1,470	1,520	4.9
960/1024GB	256GBx4, BGA TSB BiCS3	550	500	560	540	1,575	1,620	4.9
240/256GB	144GBx2, BGA, Spectek B0KB	540	490	560	540	1,320	1,630	4.9
480/512GB	144GBx4, BGA, Spectek B0KB	550	490	560	540	1,400	1,900	4.9
120/128GB	32GBx4, BGA, Spectek B16A	550	430	560	410	1,450	1,570	4.9
240/256GB	64GBx4, BGA, Spectek B17A	540	470	560	460	1,380	1,450	4.9



120/128GB	48GBx1+96GBx1, BGA, Micron B0KB	500	390	560	540	1,355	1,515	4.9
240/256GB	48GBx2+96GBx2, BGA, Micron B0KB	550	490	560	540	1,375	1,780	4.9
240GB	96GBx1+144GBx1, BGA Micron B0KB	550	400	560	540	1,350	1,750	4.9
120/128GB	32GBx4, BGA, Micron B16A	540	425	560	430	1,395	1,480	4.9
240/256GB	64GBx4, BGA, Micron B17A	550	480	560	470	1,475	1,520	4.9

NOTE:

For more details on Power Consumption, please refer to Chapter 4.2.





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1. INTRODUCTION

1.1. General Description

Phison's PS3111 M.2 2280 delivers all the advantages of flash disk technology with the Serial ATA I/II/III interface and is fully compliant with the standard Next Generation Form Factor (NGFF) called M.2 Card Format, which is generated by Intel. The PS3111 M.2 2280 is designed to operate at a maximum operating frequency of 200MHz with 30MHz external crystal. Its capacity could provide a wide range up to 512GB. Moreover, it can reach up to 550MB/s read as well as 500MB/s write high performance based on 16CE and Toggle 2.0 TLC flash (with 32MB SDR enabled and measured by CrystalDiskMark v5.0). The power consumption of the M.2 2280 is much lower than traditional hard drives, making it the best embedded solution for new platforms.

1.2. Controller Block Diagram

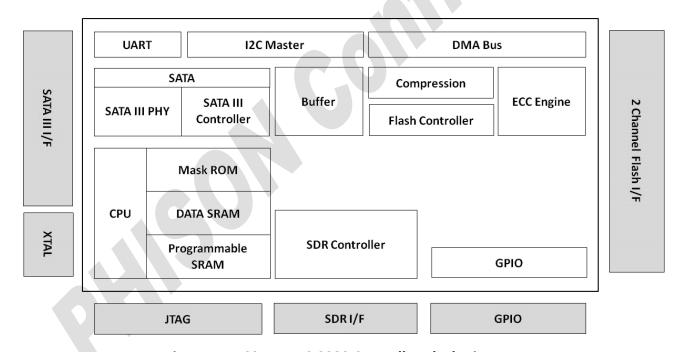


Figure 1-1 PS3111 M.2 2280 Controller Block Diagram



1.3. Product Block Diagram

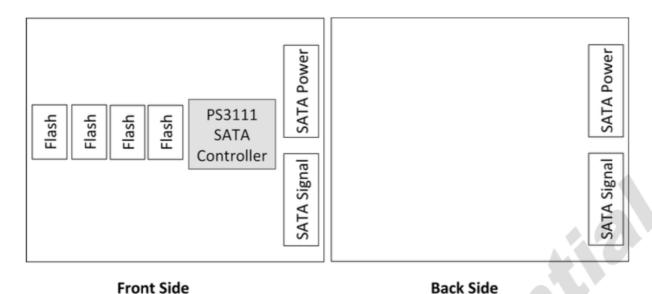


Figure 1-2 PS3111 M.2 2280 Product Block Diagram

1.4. Flash Management

1.4.1. Error Correction Code (ECC)

Flash memory cells will deteriorate with use, which might generate random bit errors in the stored data. Thus, PS3111 M.2 2280 applies the LDPC (Low Density Parity Check) of ECC algorithm, which can detect and correct errors occur during read process, ensure data been read correctly, as well as protect data from corruption.

1.4.2. Wear Leveling

NAND flash devices can only undergo a limited number of program/erase cycles, and in most cases, the flash media are not used evenly. If some areas get updated more frequently than others, the lifetime of the device would be reduced significantly. Thus, Wear Leveling is applied to extend the lifespan of NAND flash by evenly distributing write and erase cycles across the media.

Phison provides advanced Wear Leveling algorithm, which can efficiently spread out the flash usage through the whole flash media area. Moreover, by implementing both dynamic and static Wear Leveling algorithms, the life expectancy of the NAND flash is greatly improved.



1.4.3. Bad Block Management

Bad blocks are blocks that include one or more invalid bits, and their reliability is not guaranteed. Blocks that are identified and marked as bad by the manufacturer are referred to as "Initial Bad Blocks". Bad blocks that are developed during the lifespan of the flash are named "Later Bad Blocks". Phison implements an efficient bad block management algorithm to detect the factory-produced bad blocks and manages any bad blocks that appear with use. This practice further prevents data being stored into bad blocks and improves the data reliability.

1.4.4. TRIM

TRIM is a feature which helps improve the read/write performance and speed of solid-state drives (SSD). Unlike hard disk drives (HDD), SSDs are not able to overwrite existing data, so the available space gradually becomes smaller with each use. With the TRIM command, the operating system can inform the SSD which blocks of data are no longer in use and can be removed permanently. Thus, the SSD will perform the erase action, which prevents unused data from occupying blocks all the time.

1.4.5. SMART

SMART, an acronym for Self-Monitoring, Analysis and Reporting Technology, is an open standard that allows a hard disk drive to automatically detect its health and report potential failures. When a failure is recorded by SMART, users can choose to replace the drive to prevent unexpected outage or data loss. Moreover, SMART can inform users of impending failures while there is still time to perform proactive actions, such as copy data to another device.

1.4.6. Over-Provision

Over Provisioning refers to the inclusion of extra NAND capacity in a SSD, which is not visible and cannot be used by users. With Over Provisioning, the performance and IOPS (Input/Output Operations per Second) are improved by providing the controller additional space to manage P/E cycles, which enhances the reliability and endurance as well. Moreover, the write amplification of the SSD becomes lower when the controller writes data to the flash.



1.4.7. Firmware Upgrade

Firmware can be considered as a set of instructions on how the device communicates with the host. Firmware will be upgraded when new features are added, compatibility issues are fixed, or read/write performance gets improved.

1.5. Low Power Management

1.5.1. DEVSLP Mode (Optional)

With the increasing need of aggressive power/battery life, SATA interfaces include a new feature, Device Sleep (DEVSLP) mode, which helps further reduce the power consumption of the device. DEVSLP enables the device to completely power down the device PHY and other sub-systems, making the device reach a new level of lower power operation. The DEVSLP does not specify the exact power level a device can achieve in the DEVSLP mode, but the power usage can be dropped down to 5mW or less.

1.5.2. DIPM/HIPM Mode

SATA interfaces contain two low power management states for power saving: Partial and Slumber modes. For Partial mode, the device has to resume to full operation within 10 microseconds, whereas the device will spend 10 milliseconds to become fully operational in the Slumber mode. SATA interfaces allow low power modes to be initiated by Host (HIPM, Host Initiated Power Management) or Device (DIPM, Device Initiated Power Management). As for HIPM, Partial or Slumber mode can be invoked directly by the software. For DIPM, the device will send requests to enter Partial or Slumber mode.

1.6. Power Loss Protection: Flushing Mechanism (Optional)

Power Loss Protection is a mechanism to prevent data loss during unexpected power failure. DRAM is a volatile memory and frequently used as temporary cache or buffer between the controller and the NAND flash to improve the SSD performance. However, one major concern of the DRAM is that it is not able to keep data during power failure. Accordingly, the PS3111 applies the *GuaranteedFlush* technology, which requests the controller to transfer data to the cache. For PS3111, SDR performs as a cache, and its size is 32MB. Only when the data is fully committed to the NAND flash will the controller send acknowledgement (ACK) to the host. Such implementation can prevent false-positive performance and the risk of power cycling issues.



Additionally, it is critical for a controller to shorten the time the in-flight data stays in the cache. Thus, Phison's PS3111 applies an algorithm to reduce the amount of data resides in the cache to provide a better performance. This *SmartCacheFlush* technology allows incoming data to only have a "pit stop" in the cache and then move to the NAND flash at once. If the flash is jammed due to particular file sizes (such as random 4KB data), the cache will be treated as an "organizer", consolidating incoming data into groups before written into the flash to improve write amplification.

In sum, with Flush Mechanism, PS3111 proves to provide the reliability required by consumer, industrial, and enterprise-level applications.

1.7. Advanced Device Security Features

1.7.1. Secure Erase

Secure Erase is a standard ATA command and will write all "0xFF" to fully wipe all the data on hard drives and SSDs. When this command is issued, the SSD controller will erase its storage blocks and return to its factory default settings.

1.7.2. Write Protect

When a SSD contains too many bad blocks and data are continuously written in, then the SSD might not be usable anymore. Thus, Write Protect is a mechanism to prevent data from being written in and protect the accuracy of data that are already stored in the SSD.

1.8. SSD Lifetime Management

1.8.1. Thermal Monitor (Optional)

Thermal monitors are devices for measuring temperature, and can be found in SSDs in order to issue warnings when SSDs go beyond a certain temperature. The higher temperature the thermal monitor detects, the more power the SSD consumes, causing the SSD to get aging quickly. Hence, the processing speed of a SSD should be under control to prevent temperature from exceeding a certain range. Meanwhile, the SSD can achieve power savings.

1.9. An Adaptive Approach to Performance Tuning



1.9.1. Throughput

Based on the available space of the disk, PS3111 will regulate the read/write speed and manage the performance of throughput. When there still remains a lot of space, the firmware will continuously perform read/write action. There is still no need to implement garbage collection to allocate and release memory, which will accelerate the read/write processing to improve the performance. Contrarily, when the space is going to be used up, PS3111 will slow down the read/write processing, and implement garbage collection to release memory. Hence, read/write performance will become slower.

1.9.2. Predict & Fetch

Normally, when the host tries to read data from the SSD, the SSD will only perform one read action after receiving one command. However, PS3111 applies *Predict & Fetch* to improve the read speed. When the host issues sequential read commands to the SSD, the SSD will automatically expect that the following will also be read commands. Thus, before receiving the next command, flash has already prepared the data. Accordingly, this accelerates the data processing time, and the host does not need to wait so long to receive data.

1.9.3. SmartZIP™

Write data to the NAND Flash costs time. To improve the write speed performance, PS3111 launches with compression technique—SmartZIP TM .

Whether a file could be compressed or not depending on the file type, for file types have redundancy data pattern, through our embedded encode engine, we could reduce the amount of data that is actually written to the Flash. Comparing to the SSD without the compression, write efficiency is raised and the SSD endurance is also improved since Flash could be benefit from less data written for a longer SSD lifetime.



2. PRODUCT SPECIFICATIONS

Capacity

- From 16GB up to 960/1024GB (support 48-bit addressing mode)
- Electrical/Physical Interface
 - SATA Interface
 - ♦ Compliant with SATA Revision 3.2
 - Compatible with SATA 1.5Gbps, 3Gbps and 6Gbps interface
 - ♦ Support power management
 - ♦ Support expanded register for SATA protocol 48 bits addressing mode
 - ♦ Embedded BIST function for SATA PHY for low cost mass production

Built-in 2-channel NAND flash interface controller

- Compliant with Toggle 1.0 and Toggle 2.0 NAND Flash interface
- Compliant with ONFI 4.0 interface:
 - ♦ SDR up to mode 5
 - ♦ NV-DDR up to mode 5
 - ♦ NV-DDR2 up to mode 7
 - NV-DDR3 up to mode 8

Supported NAND Flash

- Support up to 16 Flash Chip Enables (CE) within single design
- Toshiba 24nm SLC; 15nm/3D-NAND MLC; 15nm/3D-NAND TLC
- Intel/Micron 16nm/3D-NAND MLC and TLC
- Hynix 16nm/3D-NAND
- Support all types of SLC/MLC/TLC/3D-NAND, 8KB/page and 16K/page NAND flash
- Support ONFI 2.3, ONFI 3.0, ONFI 3.2 and ONFI 4.0 interface: 2 channels at maximum
- Support 8-bit I/O NAND Flash
- Contain 1pcs to 4pcs of TSOP/BGA flash

ECC Scheme

- PS3111 M.2 2280 applies the LDPC (Low Density Parity Check) of ECC algorithm.
- UART function
- GPIO
- Support SMART and TRIM commands



Performance

			Seque	ntial
Capacity	Flash Structure	Flash Type	Read	Write
			(MB/s)	(MB/s)
120/128GB	32GB x 4	TSOP, TSB 15nm	550	450
120/128GB	64GB x 2	TSOP, TSB 15nm	550	460
240/256GB	64GB x 4	TSOP, TSB 15nm	550	450
480/512GB	128GB x 4	TSOP, TSB 15nm	530	410
240/256GB	128GB x 2	BGA, TSB 15nm	550	450
120GB	64GB x 2	BGA, Hynix 16nm	550	380
240GB	64GB x 4	BGA, Hynix 16nm	550	480
32GB	32GB x 1	TSOP, TSB BiCS2	290	90
64GB	32GB x 2	TSOP, TSB BiCS2	550	175
120/128GB	64GB x 2	TSOP, TSB BiCS2	550	350
240/256GB	64GB x 4	TSOP, TSB BiCS2	550	490
480/512GB	128GB x 4	TSOP, TSB BiCS2	550	490
240/256GB	256GB x 1	BGA, TSB BiCS2	550	375
480/512GB	256GB x 2	BGA, TSB BiCS2	550	455
960/1024GB	256GB x 4	BGA, TSB BiCS2	550	490
16GB	16GBx1	TSOP, TSB BiCS3	290	100
30/32GB	32GBx1	TSOP, TSB BiCS3	300	125
60/64GB	32GBx2	TSOP, TSB BiCS3	550	255
120/128GB	64GBx2	TSOP, TSB BiCS3	550	450
240/256GB	64GBx4, 128GBx2	TSOP, TSB BiCS3	550	490
480/512GB	128GB x 4	TSOP, TSB BiCS3	550	490
60/64GB	64GB x 1	BGA, TSB BiCS3	550	255
120/128GB	64GB x 2	BGA, TSB BiCS3	550	450
240/256GB	64GB x 4	BGA, TSB BiCS3	550	490
240/256GB	128GB x 2	BGA, TSB BiCS3	550	490
480/512GB	256GB x 2	BGA, TSB BiCS3	550	490
960/1024GB	256GB x 4	BGA, TSB BiCS3	550	500
240/256GB	144GBx2	BGA, Spectek B0KB	540	490
480/512GB	144GBx4	BGA, Spectek BOKB	550	490
120/128GB	32GBx4	BGA, Spectek B16A	550	430
240/256GB	64GBx4	BGA, Spectek B17A	540	470
120/128GB	32GB x 4	BGA, Micron B16A	540	425
240/256GB	64GB x 4	BGA, Micron B17A	550	480
120/128GB	48GBx1+96GBx1	BGA, Micron B0KB	500	390



240/256GB	48GBx2+96GBx2	BGA, Micron B0KB	550	490
240GB	96GB x 1+144GB x 1	BGA, Micron B0KB	550	400

NOTES:

- 1. The performance was measured using CrystalDiskMarkv5.0x64 with SATA 6Gbps host.
- 2. Samples were built using Toshiba 15nm, Hynix 16nm, Toshiba Bics2, Bics3 and Micron/Spectek BOKB, B16A, B17A TLC NAND.
- 3. Performance may differ according to flash configuration and platform.
- 4. The table above is for reference only. The criteria for MP (mass production) and for accepting goods shall be discussed based on different flash configuration.



3. ENVIRONMENTAL SPECIFICATIONS

3.1. Environmental Conditions

3.1.1. Temperature and Humidity

• Temperature:

Storage: -40°C to 85°COperational: 0°C to 70°C

Humidity: RH 90% under 40°C (operational)

Table 3-1 High Temperature Test Condition

	Temperature	Humidity	Test Time
Operation	70°C	0% RH	72 hours
Storage	85°C	0% RH	72 hours

Result: No any abnormality is detected.

Table 3-2 Low Temperature Test Condition

	Temperature	Humidity	Test Time
Operation	0°C	0% RH	72 hours
Storage	-40°C	0% RH	72 hours

Result: No any abnormality is detected.

Table 3-3 High Humidity Test Condition

	Temperature	Humidity	Test Time
Operation	40°C	90% RH	4 hours
Storage	40°C	93% RH	72 hours

Result: No any abnormality is detected.

Table 3-4 Temperature Cycle Test

	Temperature	Test Time	Cycle		
Operation	0°C	30 min	10 Cycles		
	70°C	30 min	10 Cycles		
Storage	-40°C	30 min	10 Oveles		
	85°C	30 min	10 Cycles		

Result: No any abnormality is detected.



3.1.2. Shock

Table 3-5 PS3111 M.2 2280 Shock Specification

	Acceleration Force	Half Sin Pulse Duration		
Non-operational	1500G	0.5ms		

Result: No any abnormality is detected when power on.

3.1.3. Vibration

Table 3-6 PS3111 M.2 2280 Vibration Specification

	Cond	Vibration Orientation		
	Frequency/Displacement	Frequency/Acceleration	Vibration Orientation	
Non-operational	20Hz~80Hz/1.52mm	80Hz~2000Hz/20G	X, Y, Z axis/60 min for	
			each	

Result: No any abnormality is detected when power on.

3.1.4. Drop

Table 3-7 PS3111 M.2 2280 Drop Specification

	Height of Drop	Number of Drop		
Non-operational	80cm free fall	6 face of each unit		

Result: No any abnormality is detected when power on.

3.1.5. Bending

Table 3-8 PS3111 M.2 2280 Bending Specification

	Force	Action
Non-operational	≥ 20N	Hold 1min/5times

Result: No any abnormality is detected when power on.

3.1.6. Torque

Table 3-9 PS3111 M.2 2280 Torque Specification

	Force	Action
Non-operational	0.5N-m or ±2.5 deg	Hold 1min/5times

Result: No any abnormality is detected when power on.



3.1.7. Electrostatic Discharge (ESD)

Table 3-10 PS3111 M.2 2280 Contact ESD Specification

Device	Capacity	Temperature	Relative Humidity	+/- 4KV	Result
				Device functions are affected,	
M.2 2280	4.70	1TB 24.0°C	49% (RH)	but EUT will be back to its	DACC
	TIR			normal or operational state	PASS
				automatically.	

3.1.8. EMI Compliance

FCC: CISPR22CE: EN55022BSMI 13438

3.2. MTBF

MTBF, an acronym for Mean Time Between Failures, is a measure of a device's reliability. Its value represents the average time between a repair and the next failure. The measure is typically in units of hours. The higher the MTBF value, the higher the reliability of the device. The predicted result of Phison's PS3111 M.2 2280 is more than 2,000,000 hours.

3.3. Certification & Compliance

- RoHS
- SATA III (SATA Rev. 3.2)
- Up to ATA/ATAPI-8 (Including S.M.A.R.T)



4. ELECTRICAL SPECIFICATIONS

4.1. Supply Voltage

Table 4-1 Supply Voltage of PS3111 M.2 2280

Parameter	Rating
Operating Voltage	3.3V

4.2. Power Consumption

Table 4-2 Power Consumption of PS3111 M.2 2280

Capacity	Flash Structure	Flash Type	Read	Write	Partial	Slumber	Idle	DEVSLP
120/128GB	32GB x4	TSOP, TSB 15nm	1,245	1,375	13.5	8.5	265	4.9
120/128GB	64GB x2	TSOP, TSB 15nm	1,240	1,370	13.5	8.5	260	4.9
240/256GB	64GB x4	TSOP, TSB 15nm	1,425	1,850	13.5	9	270	4.9
480/512GB	128GB x4	TSOP, TSB 15nm	1,435	1,600	15.5	10	280	4.9
240/256GB	128GB x2	BGA, TSB 15nm	1,510	1,950	15	11	295	4.9
120GB	64GB x2	BGA, Hynix 16nm	1,385	1,600	14	10	300	4.9
240GB	64GB x4	BGA, Hynix 16nm	1,685	1,925	14	10	300	4.9
32GB	32GB x1	TSOP, TSB BiCS2	920	810	15	10	300	4.9
64GB	32GB x2	TSOP, TSB BiCS2	1,205	1,040	15	10	300	4.9
120/128GB	64GB x2	TSOP, TSB BiCS2	1,355	1,400	15	10	300	4.9
240/256GB	64GB x4	TSOP, TSB BiCS2	1,400	1,700	15	10	300	4.9
480/512GB	128GB x4	TSOP, TSB BiCS2	1,530	1,800	15	10	300	4.9
240/256GB	256GB x1	BGA, TSB BiCS2	1,380	1,680	16	11	300	4.9
480/512GB	256GB x2	BGA, TSB BiCS2	1,500	1,770	16	11	300	4.9
960/1024GB	256GB x4	BGA, TSB BiCS2	1,650	1,880	16	11	300	4.9
16GB	16GB x 1	TSOP, TSB BiCS3	940	840	15	10	300	4.9
30/32GB	32GB x 1	TSOP, TSB BiCS3	950	850	15	10	300	4.9
60/64GB	32GB x 2	TSOP, TSB BiCS3	1,215	1,020	15	10	300	4.9
120/128GB	64GB x 2	TSOP, TSB BiCS3	1,300	1,350	15	10	300	4.9
240/256GB	64GB x 4	TSOP, TSB BiCS3	1,350	1,400	15	10	300	4.9
480/512GB	128GB x 4	TSOP, TSB BiCS3	1,360	1,450	22	16	320	4.9
60/64GB	64GB x 1	BGA, TSB BiCS3	1,200	1,290	20	15	325	4.9
120/128GB	64GB x 2	BGA, TSB BiCS3	1,270	1,360	20	15	325	4.9
240/256GB	64GB x 4	BGA, TSB BiCS3	1,395	1,480	20	15	325	4.9
240/256GB	128GB x 2	BGA, TSB BiCS3	1,360	1,440	20	15	325	4.9
480/512GB	256GB x 2	BGA, TSB BiCS3	1,470	1,520	22	15	325	4.9
960/1024GB	256GB x 4	BGA, TSB BiCS3	1,575	1,620	22	15	325	4.9
240/256GB	144GB x 2	BGA, Spectek BOKB	1,320	1,630	18	13	300	4.9



480/512GB	144GB x 4	BGA, Spectek BOKB	1,400	1,900	20	15	300	4.9
120/128GB	32GBx4	BGA, Spectek B16A	1,450	1,570	20	15	325	4.9
240/256GB	64GBx4	BGA, Spectek B17A	1,380	1,450	20	15	325	4.9
120/128GB	32GB x 4	BGA, Micron B16A	1,395	1,480	20	15	325	4.9
240/256GB	64GB x 4	BGA, Micron B17A	1,475	1,520	22	15	325	4.9
120/128GB	48GBx1+96GBx1	BGA, Micron BOKB	1,355	1,515	14	10	300	4.9
240/256GB	48GBx2+96GBx2	BGA, Micron BOKB	1,375	1,780	14	10	300	4.9
240GB	96GB x 1+144GB x1	BGA, Micron BOKB	1,350	1,750	14	10	300	4.9

NOTES:

- 1. The average value of power consumption is achieved based on 100% conversion efficiency.
- 2. The measured power voltage is 3.3V.
- 3. Samples were built using Toshiba 15nm, Hynix 16nm, Toshiba Bics2, Bics3 and Micron/Spectek BOKB,

B16A, B17A TLC NAND.

It's measured under ambient temperature.

- 4. Sequential R/W is measured while testing 4000MB sequential R/W 5 times by CyrstalDiskMark. DEVSLP is measured while entering device sleep mode for 5 minutes.
- 5. Power Consumption may differ according to flash configuration and platform.



5. INTERFACE

5.1. Pin Assignment and Descriptions

Table 5-1 defines the signal assignment of the internal NGFF connector for SSD usage, described in the PCI Express M.2 Specification version 1.0 of the PCI-SIG.

Table 5-1 Pin Assignment and Description of PS3111 M.2 2280

Pin#	SATA Pin	Description
1	CONFIG_3	Ground
2	3.3V	Supply pin
3	GND	Ground
4	3.3V	Supply pin
5	N/C	No Connect
6	N/C	No Connect
7	N/C	No Connect
8	N/C	No Connect
9	N/C or GND Note	No Connect or Ground
		Status indicators via LED devices that will be provided by the
10	DAS/DSS# (O) (OD)	system Active Low. A pulled-up LED with series current
		limiting resistor should allow for 9mA when On.
11	N/C	No Connect
12	Module Key	
13	Module Key	
14	Module Key	
15	Module Key	
16	Module Key	
17	Module Key	
18	Module Key	
19	Module Key	
20	N/C	No Connect
21	CONFIG_0	Ground
22	N/C	No Connect
23	N/C	No Connect
24	N/C	No Connect
25	N/C	No Connect
26	N/C	No Connect
27	GND	Ground
28	N/C	No Connect

Pin #	SATA Pin	Description			
29	N/C	No Connect			
30	N/C	No Connect			
31	N/C	No Connect			
32	N/C	No Connect			
33	GND	Ground			
34	N/C	No Connect			
35	N/C	No Connect			
36	N/C	No Connect			
37	N/C	No Connect			
		Device Sleep, Input.			
38	DEVSLP (I)	When driven high the host is informing the SSD to enter a			
		low power state			
39	GND	Ground			
40	N/C	No Connect			
41	SATA-B+	SATA differential signals in the SATA specification			
42	N/C	No Connect			
43	SATA-B-	SATA differential signals in the SATA specification			
44	N/C	No Connect			
45	GND	Ground			
46	N/C	No Connect			
47	SATA-A-	SATA differential signals			
47	SAIA-A-	in the SATA specification			
48	N/C	No Connect			
49	SATA-A+	SATA differential signals			
43	JAIA-AT	in the SATA specification			
50	N/C	No Connect			
51	GND	Ground			
52	N/C	No Connect			
53	N/C	No Connect			
54	N/C	No Connect			
55	N/C	No Connect			
56	Reserved for MFG	No Connect			
30	Data	THE CONNECT			
57	GND	Ground			
58	Reserved for MFG	No Connect			
5 8	Clock	No Connect			
59	Module Key				
60	Module Key				



Pin #	SATA Pin	Description
61	Module Key	
62	Module Key	
63	Module Key	
64	Module Key	
65	Module Key	
66	Module Key	
67	N/C	No Connect
68	SUSCLK (I) (0/3.3V)	No Connect
69	CONFIG_1	Ground
70	3.3V	Supply pin
71	GND	Ground
72	3.3V	Supply pin
73	GND	Ground
74	3.3V	Supply pin
75	CONFIG_2	Ground

NOTE: N/C for Socket 2, and GND for Socket 3.



6. SUPPORTED COMMANDS

6.1. ATA Command List

The following ATA command list table is followed by ATA8-ACS4 SPEC.

Table 6-1 ATA Command List

Table 6-1 ATA Command List						
Op Code	Description	Op Code		le	Description	
00h	NOP	C9h			Read DMA without Retry	
06h	Data Set Management	CAh			Write DMA	
10h-1Fh	Recalibrate		CBh		Write DMA without Retry	
20h	Read Sectors		CEh		Write Multiple FUA EXT	
21h	Read Sectors without Retry		E0h		Standby Immediate	
24h	Read Sectors EXT		E1h		Idle Immediate	
25h	Read DMA EXT		E2h		Standby	
27h	Read Native Max Address EXT		E3h		Idle	
29h	Read Multiple EXT		E4h		Read Buffer	
2Fh	Read Log EXT		E5h		Check Power Mode	
30h	Write Sectors		E6h		Sleep	
31h	Write Sectors without Retry		E7h		Flush Cache	
34h	Write Sectors EXT		E8h		Write Buffer	
35h	Write DMA EXT		E9h		READ BUFFER DMA	
37h	Set Native Max Address EXT		EAh		Flush Cache EXT	
38h	CFA Write Sectors Without Erase		EBh		Write Buffer DMA	
39h	Write Multiple EXT	ECh			Identify Device	
3Dh	Write DMA FUA EXT	EFh			Set Features	
3Fh	Write Long EXT	EFh	EFh 02h		Enable volatile write cache	
40h	Read Verify Sectors	EFh	03	3h	Set transfer mode	
41h	Read Verify Sectors without Retry	EFh	05	5h	Enable the APM feature set	
42h	Read Verify Sectors EXT	EFh	10)h	Enable use of SATA features et	
44b	Zoro CVT	rrh	10h	02h	Enable DMA Setup FIS Auto-Activate	
44h	Zero EXT	EFh	10h	02h	optimization	
45h	Write Uncorrectable EVT	CCP	10h	02h	Enable Device-initiated interface	
4511	Write Uncorrectable EXT	EFh	10h	03h	power state (DIPM) transitions	
47h	Road Log DMA EVT	EFh	10h	06h	Enable Software Settings Preservation	
4/11	Read Log DMA EXT	EFII	10h	06h	(SSP)	
57h	Write Log DMA EVT	EFh	10h	07h	Enable Device Automatic Partial to	
3/11	Write Log DMA EXT		1011	0/11	Slumber transitions	
60h	Read FPDMA Queued	EFh	10h	09h	Enable Device Sleep	
61h	Write FPDMA Queued	EFh	55	5h	Disable read look-ahead	
70h-7Fh	Seek	EFh	EFh 66h		Disable reverting to power-on defaults	



Ор	Code	Description	0	Op Code		Description
9	0h	Execute Device Diagnostic	EFh	EFh 82h		Disable volatile write cache
9	1h	Initialize Device Parameters	EFh	EFh 85h		Disable the APM feature set
9	2h	Download Microcode	EFh	90	0h	Disable use of SATA feature set
9	3h	Download Microcode DMA	EFh	90h	02h	Disable DMA Setup FIS Auto-Activate optimization
В	0h	SMART	EFh	90h	03h	Disable Device-initiated interface power state (DIPM) transitions
B0h	D0h	SMART READ DATA	EFh	n 90h 06h		Disable Software Settings Preservation (SSP)
B0h	D1h	SMART READ ATTRIBUTE THRESHOLDS	EFh	90h 07h		Disable Device Automatic Partial to Slumber transitions
B0h	D2h	SMART ENABLE/DISABILE ATTRIBUTE AUTOSAVE	EFh	90h 09h		Disable Device Sleep
B0h	D3h	SMART SAVE ATTRIBUTE VALUES	EFh	n AAh		Enable read look-ahead
B0h	D4h	SMART EXECUTE OFF-LINE IMMEDIATE	EFh	EFh CCh		Enable reverting to power-on defaults
B0h	D5h	SMART READ LOG	F1h			Security Set Password
B0h	D6h	SMART WRITE LOG		F2h		Security Unlock
B0h	D8h	SMART ENABLE OPERATIONS		F3h		Security Erase Prepare
B0h	D9h	SMART DISABLE OPERATIONS		F4h		Security Erase Unit
B0h	DAh	SMART RETURN STATUS		F5h		Security Freeze Lock
B0h	DBh	SMART ENABLE/DISABILE AUTOMATIC OFF-LINE	F6h			Security Disable Password
В	1h	Device Configuration	F8h			Read Native Max Address
В	4h	Sanitize	F9h			Set Max Address
С	4h	Read Multiple	F9h 01h		1h	SET MAX SET PASSWORD
С	5h	Write Multiple	F9h	F9h 02h		SET MAXLOCK
С	6h	Set Multiple Mode	F9h	F9h 03h		SET MAX UNLOCK
С	8h	Read DMA	F9h	-9h 04h		SET MAX FREEZE LOCIK



6.2. Identify Device Data

The following table details the sector data returned by the IDENTIFY DEVICE command of ATA8-ACS4 SPEC.

Table 6-2 List of Device Identification

	E. Eine d			
	F: Fixed			
	V: Variable	- 6 1		
Word	X:	Default Value	Description	
	retired/obsolete			
	/reserved			
0	F	0040h	General configuration bit-significant information	
1	Х	*1	Obsolete	
2	F	C837h	Specific configuration	
3	Х	0010h	Obsolete	
4-5	Х	00000000h	Retired	
6	X	003Fh	Obsolete	
7-8	X	00000000h	Reserved for assignment by the Compact Flash	
			Association	
9	Х	0000h	Retired	
10-19	V	Varies	Serial number (20 ASCII characters)	
20-21	Х	0000000h	Retired	
22	Х	0000h	Obsolete	
23-26	V	Varies	Firmware revision (8 ASCII characters)	
27-46	V	Varies	Model number (xxxxxxxxx)	
47	F	8010h	7:0- Maximum number of sectors transferred per	
			interrupt on MULTIPLE commands	
48	F	4000h	Trusted Computing feature set options(not support)	
49	F	2F00h	Capabilities	
50	F	4000h	Capabilities	
51-52	х	000000000h	Obsolete	
53	F	0007h	Words 88 and 70:64 valid	
54	X	*1	Obsolete	
55	Х	0010h	Obsolete	
56	Х	003Fh	Obsolete	
57-58	Х	*2	Obsolete	
59	F	0110h	Sanitize and Number of sectors transferred per	
			interrupt on MULTIPLE commands	
60-61	V	*3	Maximum number of sector (28bit LBA mode)	
62	Х	0000h	Obsolete	
Word	F: Fixed	Default Value	Description	



	V: Variable		
	X:		
	retired/obsolete		
	/reserved		
63	F	0407h	Multi-word DMA modes supported/selected
64	F	0003h	PIO modes supported
65	F	0078h	Minimum Multiword DMA transfer cycle time per
			word
66	F	0078h	Manufacturer's recommended Multiword DMA
			transfer cycle time
67	F	0078h	Minimum PIO transfer cycle time without flow control
68	F	0078h	Minimum PIO transfer cycle time with IORDY flow
			control
69	F	1F00h	Additional Supported (support download microcode
			DMA)
70	X	0000h	Reserved
71-74	Х	00000000000	Reserved for the IDENTIFY PACKET DEVICE command
		0000h	
75	F	001Fh	Queue depth
76	F	850Eh	Serial SATA capabilities
77	F	0006h	Serial ATA Additional Capabilities
78	F	004Ch	Serial ATA features supported
79	F	0040h	Serial ATA features enabled
80	F	0FF8h	Major Version Number
81	F	0000h	Minor Version Number
82	F	746Bh	Command set supported
83	F	7D01h	Command set supported
84	F	4163h	Command set/feature supported extension
85	F	7469h	Command set/feature enabled
86	F	BC01h	Command set/feature enabled
87	F	4163h	Command set/feature default
88	F	007Fh	Ultra DMA Modes
89	F	000ah	Time required for security erase unit completion
90	F	001Eh	Time required for Enhanced security erase completion
91	F	0000h	Current advanced power management value
92	F	FFFEh	Master Password Revision Code
93	F	0000h	Hardware reset result. For SATA devices, word 93 shall
			be set to the value 0000h.
Word	F: Fixed	Default Value	Description

	V: Variable X:		
	retired/obsolete		
	/reserved		
94	Х	0000h	Obsolete
95	F	0000h	Stream Minimum Request Size
96	F	0000h	Streaming Transfer Time – DMA
97	F	0000h	Streaming Access Latency – DMA and PIO
98-99	F	00000000h	Streaming Performance Granularity
100-103	V	*4	Maximum user LBA for 48 bit Address feature set
104	F	0000h	Streaming Transfer Time – PIO
105	F	0008h	Maximum number of 512-byte blocks per DATA SET
			MANAGEMENT command
106	F	4000h	Physical sector size/Logical sector size
107	F	0000h	Inter-seek delay for ISO-7779 acoustic testing in
			microseconds
108-111	V	Varies	World Wide Name
112-115	Х	00000000000	Reserved
		0000h	
116	X	0000h	Reserved
117-118	F	00000000h	Words per logical Sector
119	F	401Ch	Supported settings
120	F	401Ch	Command set/Feature Enabled/Supported
121-126	Х	0h	Reserved
127	X	0000h	Obsolete
128	F	0021h	Security status
129-140	V	Varies	Vendor specific
141	V	Varies	Vendor specific
142-159	V	Varies	Vendor specific
160	X	0000h	Reserved for CFA
161-167	X	0h	Reserved for CFA
168	V	Varies	Device Nominal Form Factor
169	F	0001h	DATA SET MANAGEMENT command is supported
170-173	F	00000000000	Additional Product Identifier
		000	
		0h	
174-175	Х	00000000h	Reserved
176-205	F	0h	Current media serial number



Word	F: Fixed V: Variable X: retired/obsolete /reserved	Default Value	Description
206	F	0000h	SCT Command Transport
207-208	X	00000000h	Reserved
209	F	4000h	Alignment of logical blocks within a physical block
210-211	F	00000000h	Write-Read-Verify Sector Count Mode 3 (not support)
212-213	F	00000000h	Write-Read-Verify Sector Count Mode 2 (not support)
214-216	X	0h	Obsolete
217	F	0001h	Non-rotating media device
218	X	0000h	Reserved
219	Х	0000h	NV Cache relate (not support)
220	V	0000h	Write read verify feature set current mode
221	X	0000h	Reserved
222	F	10FFh	Transport major version number
223	F	0000h	Transport minor version number
224-229	Х	0h	Reserved
230-233	F	00000000000 0000h	Extend number of user addressable sectors
234	F	0001h	Minimum number of 512-byte data blocks per DOWNLOAD MICROCODE command for mode 03h
235	F	FFFEh	Maximum number of 512-byte data blocks per DOWNLOAD MICROCODE command for mode 03h
236-254	X	0h	Reserved
255	F	XXA5h XX is variable	Integrity word (Checksum and Signature)



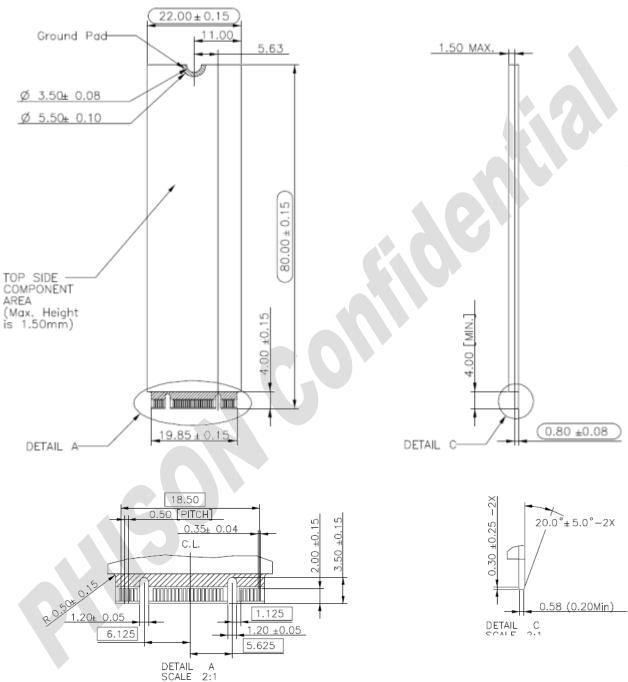
Table 6-3 List of Device Identification for Each Capacity

Capacity	*1	*2	*3	*4
(GB)	(Word 1/Word 54)	(Word 57 – 58)	(Word 60 – 61)	(Word 100 – 103)
32	3FFFh	FBFC10h	3BA2EB0h	3BA2EB0h
64	3FFFh	FBFC10h	7740AB0h	7740AB0h
120	3FFFh	FBFC10h	DF94BB0h	DF94BB0h
128	3FFFh	FBFC10h	EE7C2B0h	EE7C2B0h
240	3FFFh	FBFC10h	FFFFFFFh	1BF244B0h
256	3FFFh	FBFC10h	FFFFFFFh	1DCF32B0h
480	3FFFh	FBFC10h	FFFFFFFh	37E436B0h
512	3FFFh	FBFC10h	FFFFFFFh	3B9E12B0h
960	3FFFh	FBFC10h	FFFFFFFh	6FC81AB0h
1024	3FFFh	FBFC10h	FFFFFFh	773BD2B0h



7. PHYSICAL DIMENSION

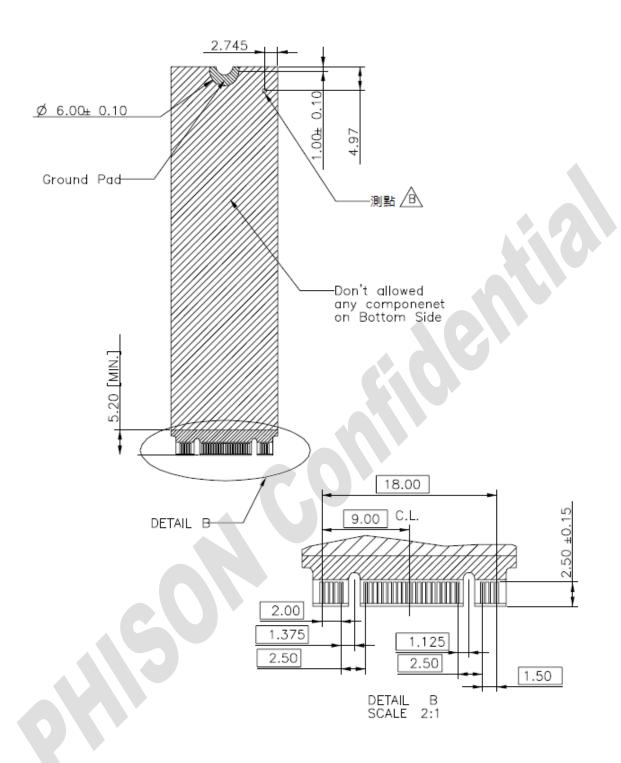
Dimension: 80±0.15mm (L) x 22±0.15mm (W) x 2.3±0.08mm (H)



Notes:

- Max Component Height
 Max Component Height
 Max Component
 Signal Vias / Signal Copper / Printing
- 4. General Tolerance ± 0.15 mm
- 5. is IQC inspection dimension







8. PRODUCT WARRANTY POLICY

In the event the Product does not conform to the specification within Phison agreed warranty period and such inconformity is solely attributable to Phison's cause, Phison agrees at its discretion replace or repair the nonconforming Product. Notwithstanding the foregoing, the aforementioned warranty shall exclude the inconformity arising from, in relation to or associated with:

- (1) alternation, modification, improper use, misuse or excessive use of the Product;
- (2) failure to comply with Phison's instructions;
- (3) Phison's compliance with customer (including customer's suppliers, subcontractors or downstream customers) indicated instructions, technologies, designs, specifications, materials, components, parts;
- (4) combination of the Product with other materials, components, parts, goods, hardware, firmware or software not developed by Phison; or
- (5) other error or failure not solely attributable to Phison's cause (including without limitation, normal wear or tear, manufacturing or assembly wastage, improper operation, virus, unauthorized maintenance or repair).

EXCEPT FOR THE ABOVE EXPRESS LIMITED WARRANTY, THE PRODUCT IS PROVIDED "AS IS," AND PHISON MAKES NO OTHER WARRANTIES (WHETHER EXPRESS, IMPLIED, STATUTORY OR OTHERWISE) REGARDING THE PRODUCT OR ANY PORTION OF IT. PHISON SPECIFICALLY DISCLAIMS ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, NONINFRINGEMENT. UNLESS OTHERWISE PHISON AGREED IN WRITING, PHISON DOES NOT RECOMMEND NOR WARANT PRODUCTS FOR USE IN LIFE SUPPORT, NUCLEAR, MEDICAL, MILITARY, TRANSPORTATION, AUTOMOTIVE, AVIATION, AEROSPACE INDUSTRY OR OTHER APPLICATIONS WHEREIN A FAILURE OR DEFECT OF THE PRODUCT MAY THREATEN LIFE, INJURY, HEALTH, LOSS OF SIGNIFICANT AMOUNT OF MONEY ("CRITICAL USE"), AND CUSTOMER AND USER HEREBY ASSUMES ALL RISK OF ANY CRITICAL USE OF THE PRODUCT.



9. REFERENCES

The following table is to list out the standards that have been adopted for designing the product.

Table 9-1 List of References

Title	Acronym/Source		
RoHS	Restriction of Hazardous Substances Directive; for further information,		
KUIIS	please contact us at sales@phison.com or support@phison.com .		
M.2	http://www.pcisig.com		
Serial ATA Revision 3.2	http://www.sata-io.org		
ATA-8 spec	http://www.t13.org		
FCC: CISPR22	Federal Communications Commission; for further information, please		
FCC: CISPR22	contact us at sales@phison.com or support@phison.com .		
CE: EN55022	Consumer electronics certification; for further information, please		
CE: EN55022	contact us at sales@phison.com or support@phison.com .		
	The Bureau of Standards, Metrology and Inspection; for further		
BSMI: 13438	information, please contact us at sales@phison.com or		
	support@phison.com.		



10. TERMINOLOGY

The following table is to list out the acronyms that have been applied throughout the document.

Table 10-1 List of Terminology

Term	Definitions
ATTO	Commercial performance benchmark application
DEVSLP	Device sleep mode
DIPM	Device initiated power management
HIPM	Host initiated power management
LBA	Logical block addressing
MB	Mega-byte
MTBF	Mean time between failures
NCQ	Native command queue
SATA	Serial advanced technology attachment
SDR	Synchronous dynamic access memory
S.M.A.R.T.	Self-monitoring, analysis and reporting technology
SSD	Solid state disk